

2SC5739

Silicon NPN epitaxial planar type

Power supply for Audio & Visual equipments

such as TVs and VCRs

Industrial equipments such as DC-DC converters

■ Features

- High-speed switching (t_{stg} : storage time/ t_f : fall time is short)
- Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Superior forward current transfer ratio h_{FE} linearity
- TO-220D built-in: Excellent package with withstand voltage 5 kV guaranteed

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	60	V
Collector-emitter voltage (Base open)	V _{CEO}	60	V
Emitter-base voltage (Collector open)	V _{EBO}	6	V
Collector current	I _C	3	A
Peak collector current *	I _{CP}	6	A
Collector power dissipation	P _C	20	W
		2.0	
	T _a = 25°C		
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note) *: Non-repetitive peak collector current

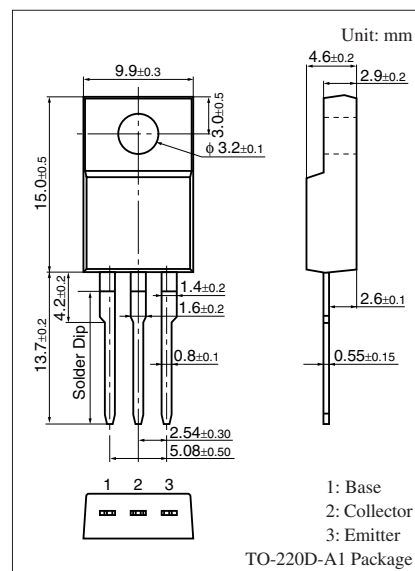
■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 10 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\text{CB}} = 60 \text{ V}, I_E = 0$			100	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{\text{CE}} = 60 \text{ V}, I_B = 0$			100	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{\text{EB}} = 6 \text{ V}, I_C = 0$			1	mA
Forward current transfer ratio	h_{FE1}^*	$V_{\text{CE}} = 4 \text{ V}, I_C = 1 \text{ A}$	120		320	—
	h_{FE2}	$V_{\text{CE}} = 4 \text{ V}, I_C = 3 \text{ A}$	40			
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_C = 3 \text{ A}, I_B = 0.375 \text{ A}$			0.5	V
Transition frequency	f_T	$V_{\text{CE}} = 10 \text{ V}, I_C = 0.1 \text{ A}, f = 10 \text{ MHz}$		180		MHz
Turn-on time	t_{on}	$I_C = 1 \text{ A}$, Resistance loaded		0.2	0.3	μs
Storage time	t_{stg}	$I_{\text{B1}} = 0.1 \text{ A}, I_{\text{B2}} = -0.1 \text{ A}$		0.55	0.70	μs
Fall time	t_f	$V_{\text{CC}} = 50 \text{ V}$		0.10	0.15	μs

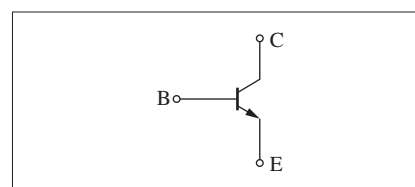
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

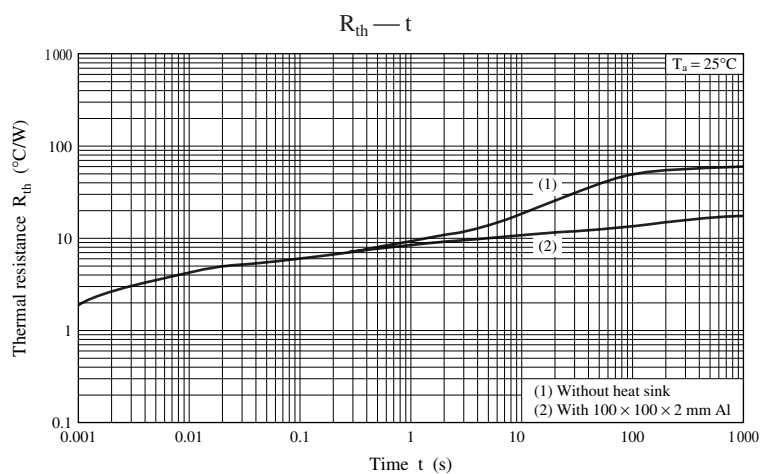
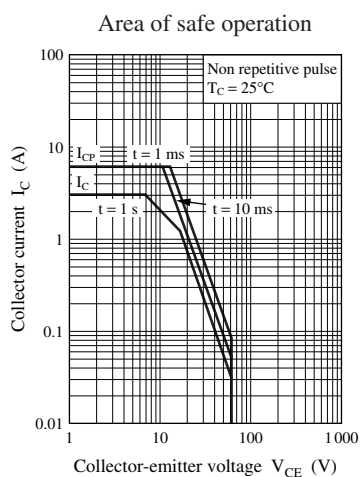
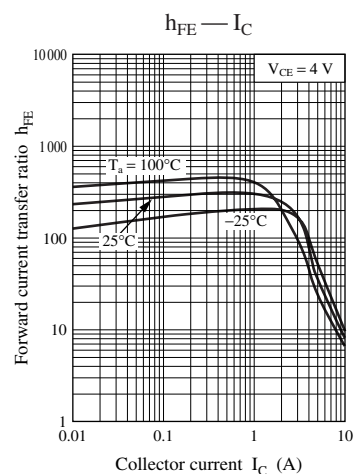
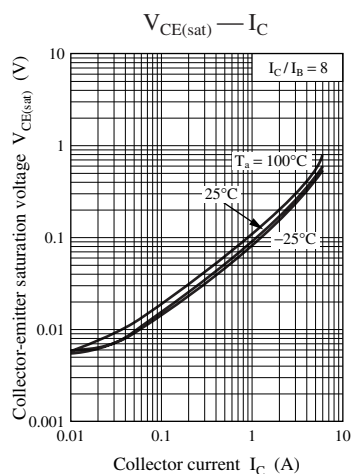
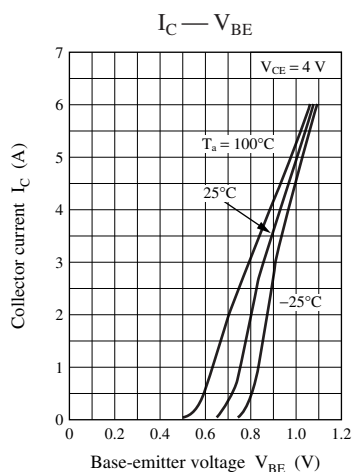
2. *: Rank classification

Rank	Q	P
h_{FE1}	120 to 250	160 to 320



Internal Connection





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